

PUMH18

50 V, 100 mA NPN/NPN resistor-equipped double transistor; R1 = 4.7 k Ω , R2 = 10 k Ω

31 March 2023

Product data sheet

1. General description

NPN/NPN double Resistor-Equipped Transistor (RET) in a very small SOT363 (SC-88) Surface-Mounted Device (SMD) plastic package.

NPN/PNP complement: PUMD18 PNP/PNP complement: PUMB18

2. Features and benefits

- 100 mA output current capability
- Built-in bias resistors
- Simplifies circuit design
- · Reduces component count
- Reduces pick and place costs
- AEC-Q101 qualified

3. Applications

- Low current peripheral driver
- Control of IC inputs
- · Replacement of general-purpose transistors in digital applications

4. Quick reference data

Table 1. Quick reference data

Table 1. Quiek reference data							
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transisto	r		·	·	·	·	·
V _{CEO}	collector-emitter voltage	open base		-	-	50	V
Io	output current			-	-	100	mA
R1	bias resistor 1 (input)		[1]	3.3	4.7	6.1	kΩ
R2/R1	bias resistor ratio		[1]	1.7	2.1	2.6	

[1] See section "Test information" for resistor calculation and test conditions.



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	GND1	GND (emitter) TR1		O1 I2 GND2
2	I1	input (base) TR1		
3	O2	output (collector) TR2	6 5 4	R1 R2
4	GND2	GND (emitter) TR2		TR2
5	12	input (base) TR2		TR1 R2 R1
6	01	output (collector) TR1	☐1 ☐2 ☐3 TSSOP6 (SOT363)	GND1 I1 O2 aaa-019894

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PUMH18		plastic, surface-mounted package; 6 leads; 0.65 mm pitch; 2.1 mm x 1.25 mm x 0.95 mm body	<u>SOT363</u>

7. Marking

Table 4. Marking codes

Type number	Marking code[1]
PUMH18	н5%

[1] % = placeholder for manufacturing site code

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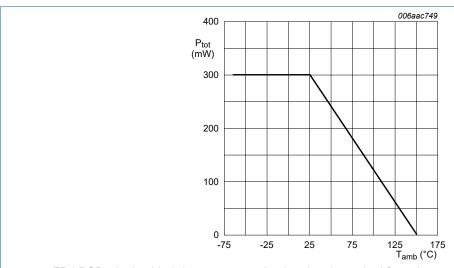
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transisto	r					
V_{CBO}	collector-base voltage	open emitter		-	50	V
V_{CEO}	collector-emitter voltage	open base		-	50	V
V _{EBO}	emitter-base voltage	open collector		-	7	V
VI	input voltage			-7	20	V
I _O	output current			-	100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	200	mW
Per device						
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	300	mW
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-65	150	°C
T _{stg}	storage temperature			-65	150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



FR4 PCB, single-sided, 35 µm copper, tin-plated and standard footprint

Fig. 1. Per device: Power derating curve

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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor							
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	625	K/W
Per device							
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	417	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

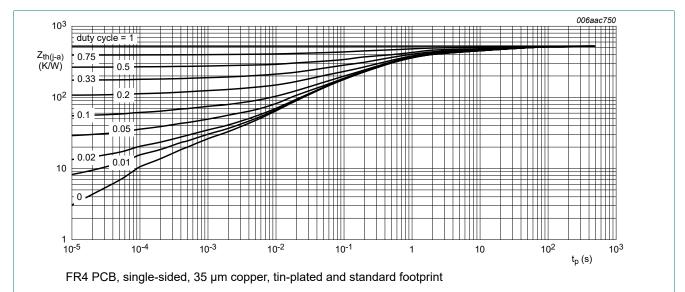


Fig. 2. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

50 V, 100 mA NPN/NPN resistor-equipped double transistor; R1 = 4.7 k Ω , R2 = 10 k Ω

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transist	or						
V _{(BR)CBO}	collector-base breakdown voltage	$I_C = 100 \ \mu A; I_E = 0 \ A; T_{amb} = 25 \ ^{\circ}C$		50	-	-	V
V _{(BR)CEO}	collector-emitter breakdown voltage	$I_C = 2 \text{ mA}; I_B = 0 \text{ A}; T_{amb} = 25 ^{\circ}\text{C}$		50	-	-	V
I _{CBO}	collector-base cut-off current	V _{CB} = 50 V; I _E = 0 A; T _{amb} = 25 °C		-	-	100	nA
I _{CEO}	collector-emitter cut-off	V _{CE} = 30 V; I _B = 0 A; T _{amb} = 25 °C		-	-	100	nA
current		V _{CE} = 30 V; I _B = 0 A; T _j = 150 °C		-	-	5	μΑ
I _{EBO}	emitter-base cut-off current	V _{EB} = 5 V; I _C = 0 A; T _{amb} = 25 °C		-	-	600	μΑ
h _{FE}	DC current gain	V _{CE} = 5 V; I _C = 10 mA; T _{amb} = 25 °C		50	-	-	
V _{CEsat}	collector-emitter saturation voltage	$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$		-	-	100	mV
V _{I(off)}	off-state input voltage	V _{CE} = 5 V; I _C = 100 μA; T _{amb} = 25 °C		-	0.9	0.3	V
V _{I(on)}	on-state input voltage	$V_{CE} = 0.3 \text{ V}; I_{C} = 20 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$		2.5	1.5	-	V
R1	bias resistor 1 (input)		[1]	3.3	4.7	6.1	kΩ
R2/R1	bias resistor ratio		[1]	1.7	2.1	2.6	
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = 0 \text{ A}; i_e = 0 \text{ A}; f = 1 \text{ MHz}; $ $T_{amb} = 25 \text{ °C}$		-	-	2.5	pF
f _T	transition frequency	V_{CE} = 5 V; I_{C} = 10 mA; f = 100 MHz; T_{amb} = 25 °C	[2]	-	230	-	MHz

- [1] See section "Test information" for resistor calculation and test conditions.
- [2] Characteristics of built-in transistor

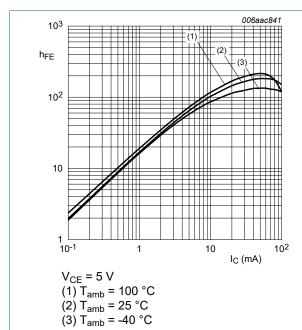


Fig. 3. DC current gain as a function of collector current; typical values

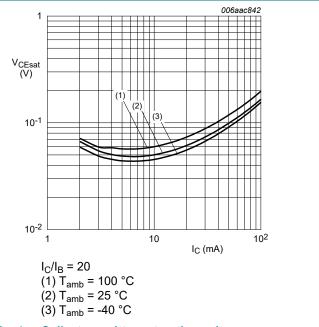
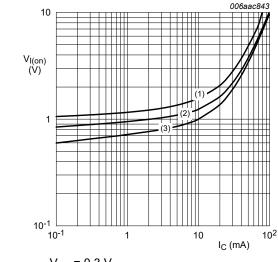


Fig. 4. Collector-emitter saturation voltage as a function of collector current; typical values

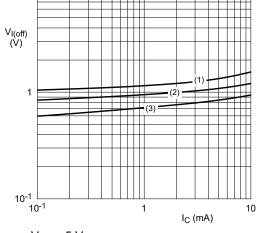
50 V, 100 mA NPN/NPN resistor-equipped double transistor; R1 = 4.7 k Ω , R2 = 10 k Ω

10



 $V_{CE} = 0.3 V$

(1) T_{amb} = -40 °C (2) T_{amb} = 25 °C (3) T_{amb} = 100 °C



006aac844

V_{CE} = 5 V (1) T_{amb} = -40 °C (2) T_{amb} = 25 °C (3) T_{amb} = 100 °C

Fig. 5. On-state input voltage as a function of collector | Fig. 6. current; typical values



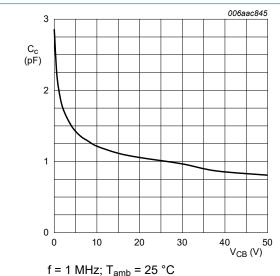
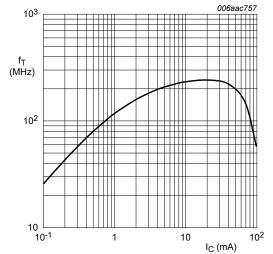


Fig. 7. Collector capacitance as a function of collector- Fig. 8. base voltage; typical values



Transition frequency as a function of collector current; typical values of built-in transistor

 V_{CE} = 5 V; T_{amb} = 25 °C

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11. Test information

Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

Resistor calculation

Calculation of bias resistor 1 (R1)

$$R_{I} = \frac{V(I_{2}) - V(I_{1})}{I_{2} - I_{1}}$$

· Calculation of bias resistor ratio (R2/R1)

$$\frac{R2}{R1} = \frac{V(I4) - V(I3)}{R1 \cdot (I4 - I3)} - 1$$

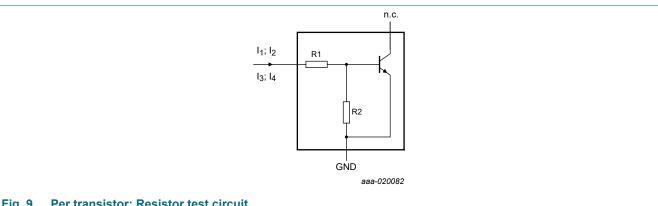


Fig. 9. Per transistor: Resistor test circuit

Resistor test conditions

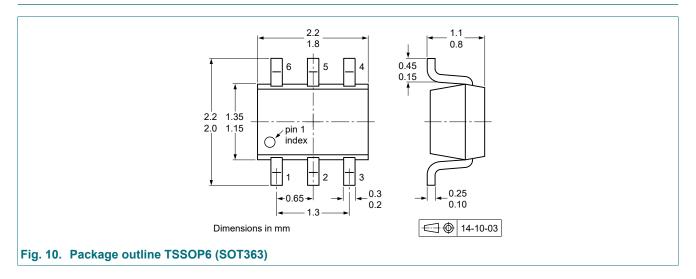
Table 8. Resistor test conditions

Type number	R1 (kΩ)	R2 (kΩ)	Test conditions				
			I ₁	l ₂	l ₃	14	
PUMH18	4.7	10	350 µA	450 µA	-350 µA	-450 μA	

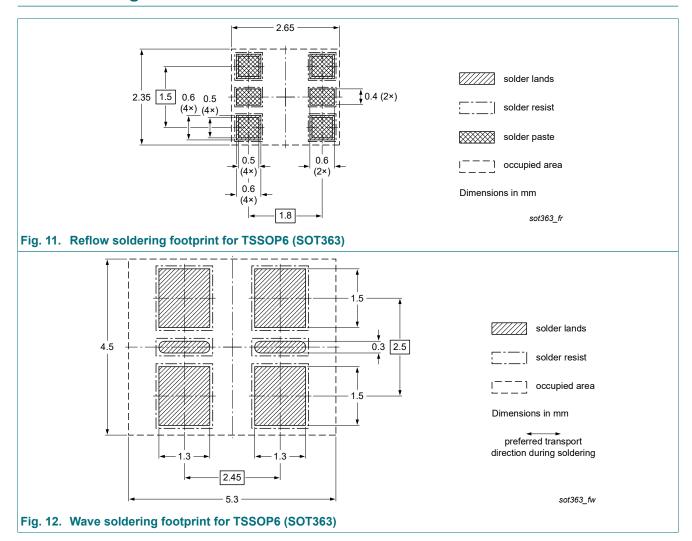
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50 V, 100 mA NPN/NPN resistor-equipped double transistor; R1 = 4.7 k Ω , R2 = 10 k Ω

12. Package outline



13. Soldering



50 V, 100 mA NPN/NPN resistor-equipped double transistor; R1 = 4.7 k Ω , R2 = 10 k Ω

14. Revision history

Table 9. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PUMH18 v.5	20230331	Product data sheet	-	PEMH18_PUMH18 v.4
Modifications:	Nexperia. • Legal texts have bee	ta sheet has been redesi en adapted to the new cor duced to single type data removed.	mpany name where appro	, ,
PEMH18_PUMH18 v.4		Product data sheet	-	PEMH18_PUMH18 v.3
PEMH18_PUMH18 v.3		Product data sheet	-	PEMH18_PUMH18 v.2
PEMH18_PUMH18 v.2		Product data sheet	-	PUMH18 v.1
PUMH18 v.1		Product specification	-	-

50 V, 100 mA NPN/NPN resistor-equipped double transistor; R1 = 4.7 k Ω , R2 = 10 k Ω

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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